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We demonstrate direct transport between two opposing sets of Yu-Shiba-Rusinov (YSR) subgap states realized in a double quantum dot. This bound-state-to-bound-state transport relies on intrinsic quasiparticle relaxation, and the tunable gating of this quantum dot device allows us to explore also an additional relaxation mechanism based on charge transferring Andreev reflections. The transition between these two relaxation regimes is identified in the experiment as a marked gate-induced stepwise change in conductance. We present a transport calculation, including YSR bound states and multiple Andreev reflections alongside quasiparticle relaxation, due to a weak tunnel coupling to a nearby normal metal, and obtain excellent agreement with the data.

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Superconductors are characterized by the existence of a Cooper-pair condensate with quasiparticle excitations, appearing above the superconducting gap $\Delta$. The interplay between superconductivity and various types of impurities [1–4], junctions [5,6], and barriers [7,8] can lead to the formation of localized quasiparticle states with energies smaller than the superconducting gap. Such subgap bound states are receiving increasing attention, as the quasiparticle parity protection offered by the gap makes them amenable to quantum coherent manipulation [9–12]. This attribute makes subgap states excellent candidates for qubits in quantum information processing. Nevertheless, many experiments have shown the existence of quasiparticle relaxation and poisoning, which break parity conservation and decohere the subgap states [6,11,13]. The physics behind relaxation and poisoning processes differs from system to system as it depends on fabrication details and on the electromagnetic environment. It is therefore a priori difficult to estimate its origin and magnitude [14–16]. The transport properties of subgap states depend strongly on the relaxation and poisoning rates and can therefore be used to probe their population dynamics [17,18]. This was demonstrated recently using scanning tunneling microscopy (STM) to measure direct transport between two sets of Yu-Shiba-Rusinov (YSR) states induced by intrinsic magnetic impurities on a vanadium (100) surface and picked up by a vanadium tip [19]. Although the microscopic nature of the impurities was largely unknown, the transport provided a clear measure of subgap dynamics independent of temperature and environmental broadening. In this Letter, we investigate direct transport between opposing YSR states arising from the interaction between superconducting leads and Coulomb blockaded quantum dots acting as spin-1/2 impurities. Compared to Ref. [19], this setup provides for well-defined YSR states, whose excitation energies can be continuously tuned by individual gates. This tunability allows us to explore the full phase diagram of available relaxation processes, which was suggested but could not be reached experimentally in Ref. [19]. To explain the transport signatures, we utilize Floquet Keldysh Green’s functions [20,21] to calculate the current across different relaxation regimes, and we demonstrate that these results can be understood in terms of master equations as in Ref. [19], which we extend here to all relaxation regimes. The interaction between a superconductor and the spin localized on a quantum dot leads to the formation of a YSR state [22–24]. The quantum dot is characterized by a charging energy $U$, a level position $\epsilon$, and a tunnel coupling to a superconductor characterized by a tunneling rate $\Gamma$. By tuning a gate voltage to change $\epsilon$, one can manipulate both the excitation energy and the ground state of the superconductor-dot system. We use an InAs nanowire-based double quantum dot (DQD) coupled to two superconductors [25–27] to obtain two independent subgap states at energies $E_L$ and $E_R$, shown schematically in Fig. 1(a). In the limit of low tunnel coupling between the dots $t_d$, compared to the dot-superconductor tunneling rates $\Gamma_L$ and $\Gamma_R$, here each dot will be in equilibrium with its respective superconductor, and a bias voltage $V$ applied across the superconductors will cause a voltage drop across the two dots. At the resonances $eV = (\pm(E_L + E_R))$, the electron component of one subgap state is aligned with the hole component of the other, and direct electron transfer can take place. This will excite both subgap systems, i.e., $|0,0\rangle \leftrightarrow |1,1\rangle$, where $0$ ($1$) denote the ground (excited) state in the corresponding left, or right, subgap system. The potential for such resonant transitions to carry a current relies entirely on the availability...
of relaxation channels to reset the subgap systems back to $|0, 0\rangle$ after each interdot tunneling process.

A diagram showing the different relaxation regimes and a schematic of available relaxation processes are presented in Figs. 1(b) and 1(c). The intrinsic relaxation processes 1 and 2, with rates $\gamma_{L/R}$, in Fig. 1(c) are active at all energies, while processes 3 and 4, with rates $\gamma_{L/R}$, only become available for subgap states with $E_{R/L} + 2E_{L/R} > \Delta_{L/R}$, where an Andreev reflection, followed by a single quasiparticle transfer to the opposing continuum, may serve to reset the subgap excitations. Since these additional relaxation channels themselves transfer charge, a full transport cycle using both processes 3 and 4 constitutes a transfer of three electrons in total. Notice that, since these additional relaxation channels themselves transfer charge, a full transport cycle using both processes 3 and 4 constitutes a transfer of three electrons in total. Notice that, unlike multiple Andreev reflection (MAR) processes between two superconductors [28], this three-electron transfer occurs incoherently. In total, one should therefore expect a higher relaxation rate $\gamma_{L/R}$ for the corresponding regime in Fig. 1(b). Arrows in the top mark cuts shown in (d) and dashed horizontal lines indicate changes in relaxation regimes from red to gray to blue. (d) Conductance vs. bias voltage along three vertical cuts in (c) placing the $eV = E_L + E_R$ resonance in different relaxation regimes, as indicated by color. Each cut is vertically displaced by 0.8$e^2/h$. The dotted line traces the movement of the resonance.

Aluminum is etched away before contact deposition to form a 350-nm-long junction. The device is equipped with a global Si/SiOx substrate backgate. A scanning tunneling micrograph of the device is shown in Fig. 2(a). Gates 1, 3, and 5 control the tunnel couplings $\Gamma_L$, $\Gamma_R$, and $\Gamma_d$, and are set to constant voltages. Plunger gates 2 and 4 control the filling of the corresponding left and right dots.

This device and its connecting circuitry have been characterized in Refs. [25,29], where it was tuned up to measure (critical) supercurrent for different regimes of YSR screening. In this work, the device is adjusted differently to explore the relaxation time. A zero-bias conductance charge diagram in logarithmic scale. Arrows labeled (a)–(f) indicate line cuts plotted in (c) and in Fig. 3. Gates 1, 3, and 5 are set to $-9.05$, $-8.7$, and 0.74 V, respectively, and the backgate is set to 11.15 V. (c) Conductance as a function of bias, and gate voltages following half the range of line cut (a) in (b) parametrized by gate 4. A vertical color bar on the right indicates relaxation regimes for $E_L = 0.058$ meV (read off as indicated) with colors indicating the corresponding regime in Fig. 1(b). Arrows in the top mark cuts shown in (d) and dashed horizontal lines indicate changes in relaxation regimes from red to gray to blue. (d) Conductance vs bias voltage along three vertical cuts in (c) placing the $eV = E_L + E_R$ resonance in different relaxation regimes, as indicated by color. Each cut is vertically displaced by 0.8$e^2/h$. The dotted line traces the movement of the resonance.
correspond to effective gaps proximitized in the InAs leads, and not the aluminum parent gap [29].

In Fig. 2(c), we show half of the gate extension of the central line cut of differential conductance versus bias and gate voltages labeled 2 in Fig. 2(b). To interpret this cut, we assume that the energy of the left subgap state $E_2$ remains constant as the right dot is gated, and identify the lowest-lying feature as the $eV = E_L + E_R$ resonance, supported by the negative differential conductance (NDC) immediately following the conductance peak. As gate 4 is tuned, a sudden change of slope occurs at $-1.236$ eV, which indicates that $E_R = 0$, signaling a change of ground state of the right dot-superconductor system, and allows us to infer that $E_L = 0.058$ meV $< \Delta_R/2$.

Strikingly, as the $eV = E_L + E_R$ feature in Fig. 2(c) moves with gate 4, stepwise changes in conductance are observed before and after the phase transition. The position of these thresholds shifts with changes in the available relaxation processes, estimated from the bound-state energies, shown as horizontal lines in Fig. 2(c) and as the path in Fig. 1(b). This path shows that as gate increases the resonance moves from red $\rightarrow$ blue $\rightarrow$ red with gray regions only observed as transitional steps. In Fig. 2(d), three line cuts show the decrease in conductance of the lowest-lying peak-dip features by approximately a factor of 4 between the top and bottom curves. This pronounced contrast in conductance marks a gate tunable transition between three different relaxation regimes.

These types of changes in conductance at special thresholds are widespread in our data and their positions match expectations from Fig. 1(b). In Fig. 3 we plot the six line cuts indicated in Fig. 2(b), where the lowest-lying feature corresponds to $eV = E_L + E_R$. From the slope of this feature we infer that the right dot is immediately coupled to the superconductor showing a characteristic eye shape, while the left dot is more strongly coupled and close to the phase transition at the particle-hole symmetric point [31]. Additional data showing similar transport with the left dot coupling tuned both stronger and weaker are shown in the Supplemental Material [30].

Additional conductance features at higher bias in Fig. 2(c) are identified as a peak at $eV = E_L + \Delta_L$ dispersing as the $eV = E_L + E_R$ feature, and a peak at $eV = E_L + \Delta_R$, which is independent of gate 4, supporting that $E_L$ remains constant as $E_R$ is tuned by gate 4. In all cuts shown in Fig. 3, replicas of the $eV = E_{L/R} + \Delta_{R/L}$ features are seen above the first such feature. In cuts (a)–(c), these appear as repetitions of the $E_{L/R} + \Delta_{R/L}$ features, while in cuts (d)–(f) features with the opposite slope of the subgap state also appear. Similar features have been observed in other devices [32,33] and we ascribe them to multiple subbands in the proximitized InAs nanowire [29]. In this scenario, a conductance peak would appear for each subband coherence peak as the bias voltage is increased [30].

We model the DQD as two Anderson models with superconducting leads and an additional interdot tunnel coupling. For simplicity, we employ a spin-polarized mean-field approximation [21,34], which is known to capture the characteristic gate dependence of the YSR state [24,35]. This artificially spin-polarized description omits interdot exchange, which is anyway negligible as $\mu_J \ll U_{L/R}$ for the chosen shell. To circumvent an artificial spin blockade, the spin-polarizing mean fields are chosen to point in orthogonal directions on each dot: $B_L = \hat{z}U_{L/2}$ and $B_R = \hat{z}U_{R/2}$ [34]. With these caveats, we regard the model as a qualitative description of the experimental situation.

To calculate the nonlinear $I$-$V$ characteristics, we employ Keldysh Floquet Green’s functions incorporating both MAR and relaxation processes. The current is $P(E)$ broadened by a Gaussian of width $\sigma = 0.04\Delta \approx 6 \mu$eV before calculating the conductance [30]. Results of the calculations are shown in Fig. 4. Parameters are kept fixed except for $\epsilon_L$ and $\epsilon_R$, which are chosen so as to match the line cuts shown in Fig. 3. Tuning rates $\Gamma_R = 6.65\Delta$ and $\Gamma_L = 4.2\Delta$ are chosen such that the gate dispersion of each YSR state independently matches the data. Intrinsic relaxation rates are assumed symmetric, $\eta_L = \eta_R$, and together with $\eta_J$ they are tuned to match the overall conductance scale and the size of conductance steps between different relaxation regimes. This gives a value of $\eta_L = \eta_R = 3.75 \times 10^{-4}\Delta$ and $\eta_J = 0.73\Delta$. In addition we use a temperature of $T = 10^{-3}\Delta$. In the calculations shown in Fig. 4, we observe the previously described $eV = E_L + E_R$ and $eV = \Delta_{L/R} + E_{R/L}$ features alongside the stepwise changes in conductance at transitions between different relaxation regimes.

Some analytical insight on the relaxation current carried at $eV = E_L + E_R$ can be obtained by solving a phenomenological master equation of the Lindblad form [36] As detailed in the Supplemental Material, this leads to a Lorentzian current peak,

$$I = e \gamma_L \gamma_R \frac{2\pi \gamma_L^2}{\hbar} \left[ L(1 + \frac{\Delta_L}{\Delta_L}) + R(1 + \frac{\Delta_R}{\Delta_R}) \right] e^{(eV - E_L - E_R)^2}. \tag{1}$$

where $\gamma_L^2 = u^2_{\downarrow}u^2_{\uparrow}d^2_{\downarrow\uparrow}$ is the rate of electron transfer between the left hole component with amplitude $u_L$, and the right electron component with amplitude $u_R$. The total relaxation rate for each side is $\Lambda_{L/R} = \eta_{L/R} + \gamma_{L/R}$ with $\eta_{L/R}$ being the intrinsic relaxation rate, and $\gamma_{L/R}$ the rate of relaxation occurring via Andreev reflections as sketched in Fig. 1(c), using Fermi’s golden rule, we infer the rates to be $\gamma_L = \pi u^2_{\uparrow \downarrow} |d_R(2E_{L} + E_{R})| d_R$ and $\gamma_R = \pi u^2_{\downarrow \uparrow} |d_L(-2E_{R} - E_{L})| d_L$ with $u_L$ (uR) being the corresponding electron (hole) component amplitudes and $d_{L/R}(E)$ the density of states at energy $E$. For the corresponding $eV = -E_L - E_R$ peak let $E_{L/R} \rightarrow -E_{L/R}$, substitute $u$ and $v$, and the above formulas apply. As shown in the Supplemental Material, these formulas perfectly match the results obtained from Keldysh Floquet Green’s functions for $eV = \pm \frac{\Delta}{2}(E_L + E_R)$. In the limit $\eta_{L/R} \gg \gamma_{L/R}, \gamma_{\nu}$, Eq. (1) reduces to Fermi’s golden rule, and the bias asymmetry reflects directly the ratio between electron and hole amplitudes, $u^2_{\downarrow}/v^2_{\uparrow}$. For $\eta_L = \eta_R$ and $\gamma_L = \gamma_R = 0$, which is the regime relevant in the blue region of Fig. 1(b), Eq. (1) reproduces the results of Ref. [19]. In the regime relevant for the present experiment, $\eta_J \gg \eta_{L/R}$ and hence $\gamma_{L/R} \gg \eta_{L/R}$ when outside of the blue region in Fig. 1(b), the bias asymmetry appears reversed compared to the Fermi’s golden rule limit [30]. Comparing Figs. 3 and 4(a) and 4(e), this asymmetry is seen to be reproduced by the transport calculation. A similar reversed asymmetry has been observed also by STM spectroscopy of YSR states probed by a superconducting continuum at $eV = E_{L/R} + \Delta_{R/L}$ [18].
Extending the master equation to include the doublet nature of the odd-parity subgap states, we find that the relaxational current generally depends on the ground state (odd-parity doublet or even-parity singlet), and that a finite spin relaxation rate $\gamma_s$ must be included in order to avoid a spin blockade. Such spin relaxation has been measured in a similar device [12]. Consistency with the experimental data requires that $\gamma_e \gg \gamma_s \gg \eta_{L,R}$ [30].

Without independent estimates of $t_{gl}$, $\Gamma_s$, and the continuum density of states $d_{L,R}(E)$, we cannot confidently extract intrinsic relaxation rates $\eta_{L,R}$. Nevertheless, a number of qualitative conclusions can be drawn: (1) We observe only very weak subgap mirages [32,37] indicative of a hard gap [30]. (2) Intrinsic relaxation must be present and be largely independent of the bound-state energy. (3) No quasiparticle poisoning, spontaneously exciting the ground state, is observed, since this would lead to lines at $eV = E_L - E_R$ [19] and $eV = \Delta_{L,R} - E_{R,L}$ [37] with opposite gate-voltage curvature. The last two observations indicate that the intrinsic relaxation is neither due to quasiparticle poisoning in the leads nor to high-energy phonon/photon modes [14]. More likely, the relaxation is due to a weak coupling to a nearby metallic lead. This could either be a small subgap density of states in the gap, or a weak tunnel element between the extended YSR state and the metallic Ti/Au leads. All three are consistent with our modeling of subgap-state relaxation as arising from a weak tunnel coupling to a large-bandwidth metallic lead, which also explains the weak low-voltage mirages observed in the experiment [30].

In conclusion, we have presented measurements of direct transport between two subgap states in a DQD setup. The electrical tunability of this setup allowed us to explore the transition between two different relaxation regimes, identified as stepwise changes in conductance along the $eV = E_L + E_R$ subgap resonance. We developed a model for the gateable subgap states, including intrinsic relaxation via weak tunnel coupling to a nearby normal metal, and a transport calculation combining MAR and relaxation was found to explain the observed signatures and provided excellent agreement with the experimental data. The presented bound-state-to-bound-state measurements hinge on the availability of intrinsic relaxation processes, yielding key insights into the underlying...
population dynamics of gateable subgap states relevant for future designs of superconducting qubits.

All data needed to evaluate the conclusions in the paper are present in the paper. Raw data used to produce the experimental figures in the paper can be found at the repository ERDA of the University of Copenhagen [41].

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